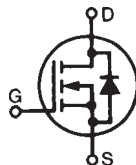


## GigaMOS™ TrenchT2 HiperFET™ Power MOSFET

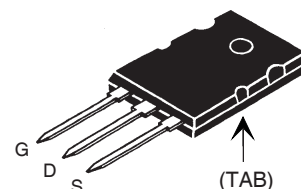
### IXFK240N15T2 IXFX240N15T2

N-Channel Enhancement Mode  
Avalanche Rated  
Fast Intrinsic Diode

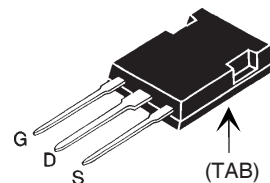


$$\begin{aligned} V_{DSS} &= 150V \\ I_{D25} &= 240A \\ R_{DS(on)} &\leq 5.2m\Omega \\ t_{rr} &\leq 140ns \end{aligned}$$

TO-264 (IXFK)



PLUS247 (IXFX)



G = Gate      D = Drain  
S = Source    TAB = Drain

| Symbol       | Test Conditions                                                    | Maximum Ratings   |                  |
|--------------|--------------------------------------------------------------------|-------------------|------------------|
| $V_{DSS}$    | $T_J = 25^\circ\text{C to } 175^\circ\text{C}$                     | 150               | V                |
| $V_{DGR}$    | $T_J = 25^\circ\text{C to } 175^\circ\text{C}, R_{GS} = 1M\Omega$  | 150               | V                |
| $V_{GSS}$    | Continuous                                                         | $\pm 20$          | V                |
| $V_{GSM}$    | Transient                                                          | $\pm 30$          | V                |
| $I_{D25}$    | $T_C = 25^\circ\text{C}$ (Chip Capability)                         | 240               | A                |
| $I_{L(RMS)}$ | External Lead Current Limit                                        | 160               | A                |
| $I_{DM}$     | $T_C = 25^\circ\text{C}$ , Pulse Width Limited by $T_{JM}$         | 600               | A                |
| $I_A$        | $T_C = 25^\circ\text{C}$                                           | 120               | A                |
| $E_{AS}$     | $T_C = 25^\circ\text{C}$                                           | 2                 | J                |
| $P_D$        | $T_C = 25^\circ\text{C}$                                           | 1250              | W                |
| $dV/dt$      | $I_S \leq I_{DM}, V_{DD} \leq V_{DSS}, T_J \leq 175^\circ\text{C}$ | 20                | V/ns             |
| $T_J$        |                                                                    | -55 ... +175      | $^\circ\text{C}$ |
| $T_{JM}$     |                                                                    | 175               | $^\circ\text{C}$ |
| $T_{stg}$    |                                                                    | -55 ... +175      | $^\circ\text{C}$ |
| $T_L$        | 1.6mm (0.062 in.) from Case for 10s                                | 300               | $^\circ\text{C}$ |
| $T_{SOLD}$   | Plastic Body for 10s                                               | 260               | $^\circ\text{C}$ |
| $M_d$        | Mounting Torque (TO-264)                                           | 1.13/10           | Nm/lb.in.        |
| $F_C$        | Mounting Force (PLUS247)                                           | 20..120 / 4.5..27 | N/lb.            |
| Weight       | TO-264                                                             | 10                | g                |
|              | PLUS247                                                            | 6                 | g                |

| Symbol       | Test Conditions<br>( $T_J = 25^\circ\text{C}$ Unless Otherwise Specified) | Characteristic Values |      |                          |
|--------------|---------------------------------------------------------------------------|-----------------------|------|--------------------------|
|              |                                                                           | Min.                  | Typ. | Max.                     |
| $BV_{DSS}$   | $V_{GS} = 0V, I_D = 3mA$                                                  | 150                   |      | V                        |
| $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_D = 8mA$                                              | 2.5                   |      | 5.0 V                    |
| $I_{GSS}$    | $V_{GS} = \pm 20V, V_{DS} = 0V$                                           |                       |      | $\pm 200$ nA             |
| $I_{DSS}$    | $V_{DS} = V_{DSS}, V_{GS} = 0V$<br>$T_J = 150^\circ\text{C}$              |                       |      | 25 $\mu\text{A}$<br>3 mA |
| $R_{DS(on)}$ | $V_{GS} = 10V, I_D = 60A$ , Note 1                                        |                       | 4.1  | 5.2 $m\Omega$            |

### Features

- International Standard Packages
- High Current Handling Capability
- Fast Intrinsic Diode
- Avalanche Rated
- Low  $R_{DS(on)}$

### Advantages

- Easy to Mount
- Space Savings
- High Power Density

### Applications

- Synchronous Rectification
- DC-DC Converters
- Battery Chargers
- Switched-Mode and Resonant-Mode Power Supplies
- DC Choppers
- AC Motor Drives
- Uninterruptible Power Supplies
- High Speed Power Switching Applications

| Symbol       | Test Conditions<br>( $T_J = 25^\circ\text{C}$ Unless Otherwise Specified)                                                                          | Characteristic Values |      |                    |
|--------------|----------------------------------------------------------------------------------------------------------------------------------------------------|-----------------------|------|--------------------|
|              |                                                                                                                                                    | Min.                  | Typ. | Max.               |
| $g_{fs}$     | $V_{DS} = 10\text{V}$ , $I_D = 60\text{A}$ , Note 1                                                                                                | 125                   | 210  | S                  |
| $C_{iss}$    | $V_{GS} = 0\text{V}$ , $V_{DS} = 25\text{V}$ , $f = 1\text{MHz}$                                                                                   |                       | 32   | nF                 |
| $C_{oss}$    |                                                                                                                                                    |                       | 2280 | pF                 |
| $C_{rss}$    |                                                                                                                                                    |                       | 270  | pF                 |
| $R_{Gi}$     | Gate Input Resistance                                                                                                                              |                       | 1.50 | $\Omega$           |
| $t_{d(on)}$  | <b>Resistive Switching Times</b><br>$V_{GS} = 10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 0.5 \cdot I_{D25}$<br>$R_G = 1\Omega$ (External) |                       | 48   | ns                 |
| $t_r$        |                                                                                                                                                    |                       | 125  | ns                 |
| $t_{d(off)}$ |                                                                                                                                                    |                       | 77   | ns                 |
| $t_f$        |                                                                                                                                                    |                       | 145  | ns                 |
| $Q_{g(on)}$  | $V_{GS} = 10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 0.5 \cdot I_{D25}$                                                                   |                       | 460  | nC                 |
| $Q_{gs}$     |                                                                                                                                                    |                       | 125  | nC                 |
| $Q_{gd}$     |                                                                                                                                                    |                       | 130  | nC                 |
| $R_{thJC}$   |                                                                                                                                                    |                       | 0.12 | $^\circ\text{C/W}$ |
| $R_{thCS}$   |                                                                                                                                                    |                       | 0.15 | $^\circ\text{C/W}$ |

## Source-Drain Diode

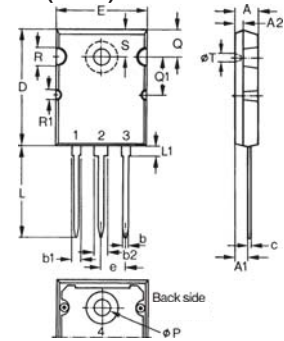
| Symbol   | Test Conditions<br>( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)                           | Characteristic Values |      |        |
|----------|-------------------------------------------------------------------------------------------------------|-----------------------|------|--------|
|          |                                                                                                       | Min.                  | Typ. | Max.   |
| $I_S$    | $V_{GS} = 0\text{V}$                                                                                  |                       |      | 240 A  |
| $I_{SM}$ | Repetitive, Pulse Width Limited by $T_{JM}$                                                           |                       |      | 960 A  |
| $V_{SD}$ | $I_F = 100\text{A}$ , $V_{GS} = 0\text{V}$ , Note 1                                                   |                       |      | 1.2 V  |
| $t_{rr}$ | $I_F = 120\text{A}$ , $-di/dt = 100\text{A}/\mu\text{s}$<br>$V_R = 75\text{V}$ , $V_{GS} = 0\text{V}$ |                       |      | 140 ns |
| $Q_{RM}$ |                                                                                                       |                       | 410  | nC     |
| $I_{RM}$ |                                                                                                       |                       | 8.2  | A      |

Note 1. Pulse test,  $t \leq 300\mu\text{s}$ ; duty cycle,  $d \leq 2\%$ .

## ADVANCE TECHNICAL INFORMATION

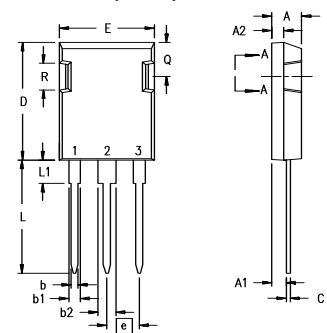
The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

## TO-264 (IXFK) Outline



| Dim. | Millimeter |       | Inches   |       |
|------|------------|-------|----------|-------|
|      | Min.       | Max.  | Min.     | Max.  |
| A    | 4.82       | 5.13  | .190     | .202  |
| A1   | 2.54       | 2.89  | .100     | .114  |
| A2   | 2.00       | 2.10  | .079     | .083  |
| b    | 1.12       | 1.42  | .044     | .056  |
| b1   | 2.39       | 2.69  | .094     | .106  |
| b2   | 2.90       | 3.09  | .114     | .122  |
| c    | 0.53       | 0.83  | .021     | .033  |
| D    | 25.91      | 26.16 | 1.020    | 1.030 |
| E    | 19.81      | 19.96 | .780     | .786  |
| e    | 5.46 BSC   |       | .215 BSC |       |
| J    | 0.00       | 0.25  | .000     | .010  |
| K    | 0.00       | 0.25  | .000     | .010  |
| L    | 20.32      | 20.83 | .800     | .820  |
| L1   | 2.29       | 2.59  | .090     | .102  |
| P    | 3.17       | 3.66  | .125     | .144  |
| Q    | 6.07       | 6.27  | .239     | .247  |
| Q1   | 8.38       | 8.69  | .330     | .342  |
| R    | 3.81       | 4.32  | .150     | .170  |
| R1   | 1.78       | 2.29  | .070     | .090  |
| S    | 6.04       | 6.30  | .238     | .248  |
| T    | 1.57       | 1.83  | .062     | .072  |

## PLUS 247™ (IXFX) Outline



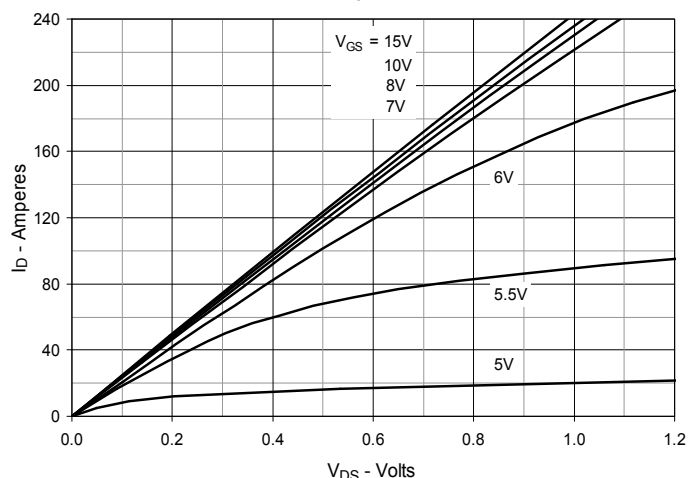
Terminals: 1 - Gate  
2 - Drain (Collector)  
3 - Source (Emitter)  
4 - Drain (Collector)

| Dim. | Millimeter |       | Inches   |      |
|------|------------|-------|----------|------|
|      | Min.       | Max.  | Min.     | Max. |
| A    | 4.83       | 5.21  | .190     | .205 |
| A1   | 2.29       | 2.54  | .090     | .100 |
| A2   | 1.91       | 2.16  | .075     | .085 |
| b    | 1.14       | 1.40  | .045     | .055 |
| b1   | 1.91       | 2.13  | .075     | .084 |
| b2   | 2.92       | 3.12  | .115     | .123 |
| C    | 0.61       | 0.80  | .024     | .031 |
| D    | 20.80      | 21.34 | .819     | .840 |
| E    | 15.75      | 16.13 | .620     | .635 |
| e    | 5.45 BSC   |       | .215 BSC |      |
| L    | 19.81      | 20.32 | .780     | .800 |
| L1   | 3.81       | 4.32  | .150     | .170 |
| Q    | 5.59       | 6.20  | .220     | .244 |
| R    | 4.32       | 4.83  | .170     | .190 |

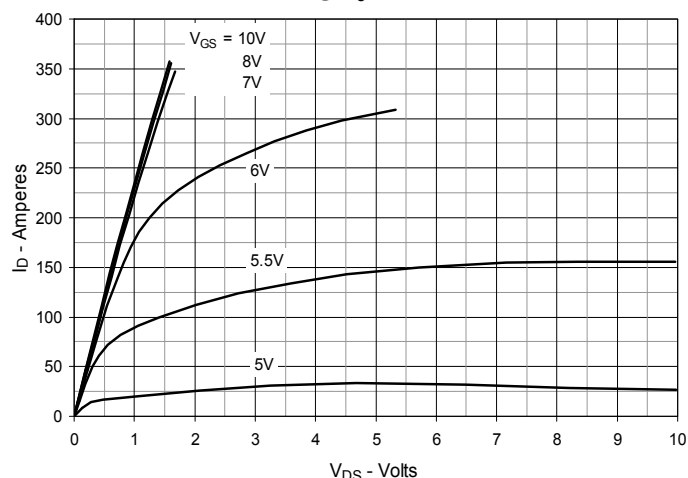
IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered 4,835,592 4,931,844 5,049,961 5,237,481 6,162,665 6,404,065 B1 6,683,344 6,727,585 7,005,734 B2 7,157,338B2  
by one or more of the following U.S. patents: 4,850,072 5,017,508 5,063,307 5,381,025 6,259,123 B1 6,534,343 6,710,405 B2 6,759,692 7,063,975 B2  
4,881,106 5,034,796 5,187,117 5,486,715 6,306,728 B1 6,583,505 6,710,463 6,771,478 B2 7,071,537

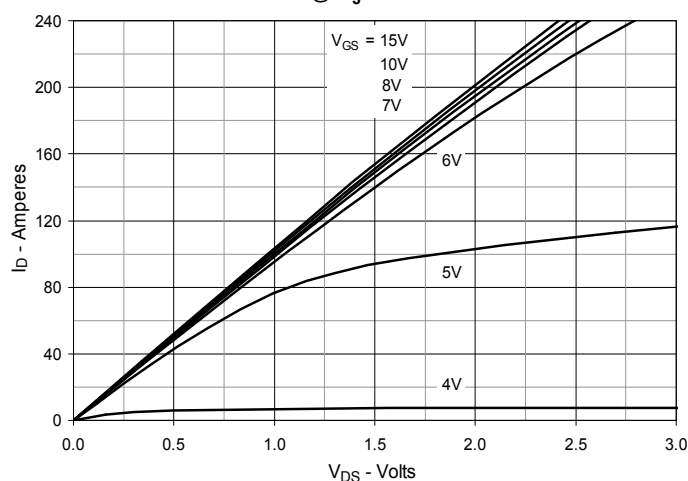
**Fig. 1. Output Characteristics**  
**@  $T_J = 25^\circ\text{C}$**



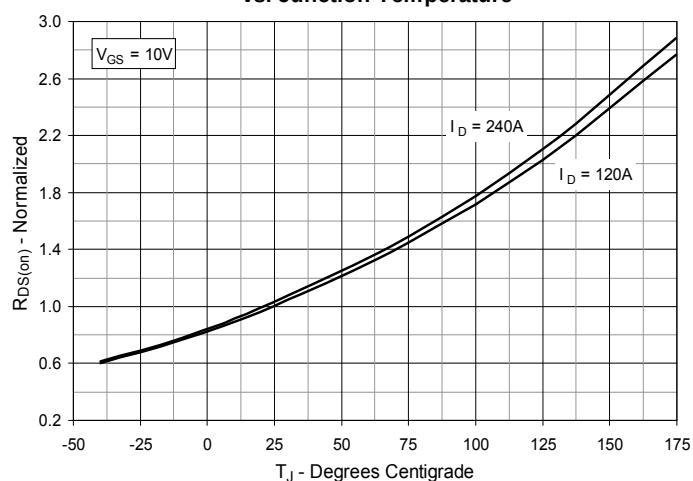
**Fig. 2. Extended Output Characteristics**  
**@  $T_J = 25^\circ\text{C}$**



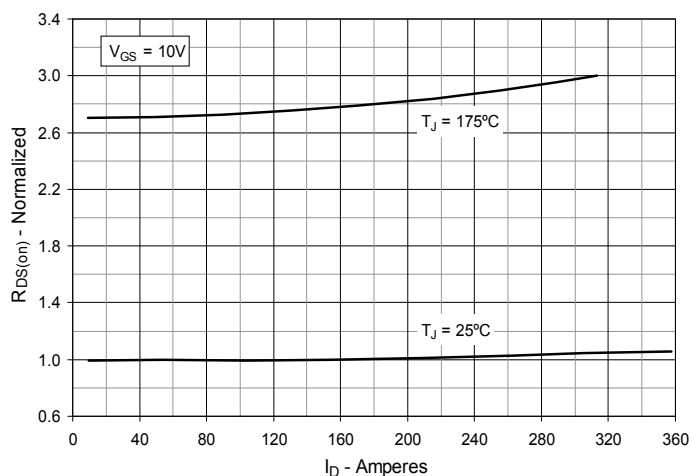
**Fig. 3. Output Characteristics**  
**@  $T_J = 150^\circ\text{C}$**



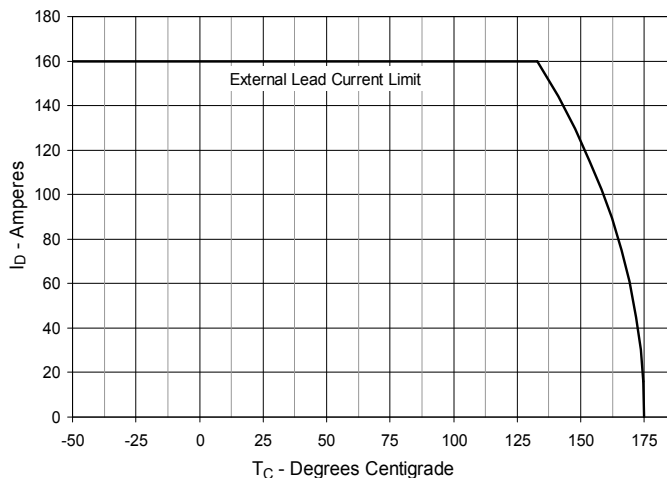
**Fig. 4.  $R_{DS(on)}$  Normalized to  $I_D = 120\text{A}$  Value**  
**vs. Junction Temperature**



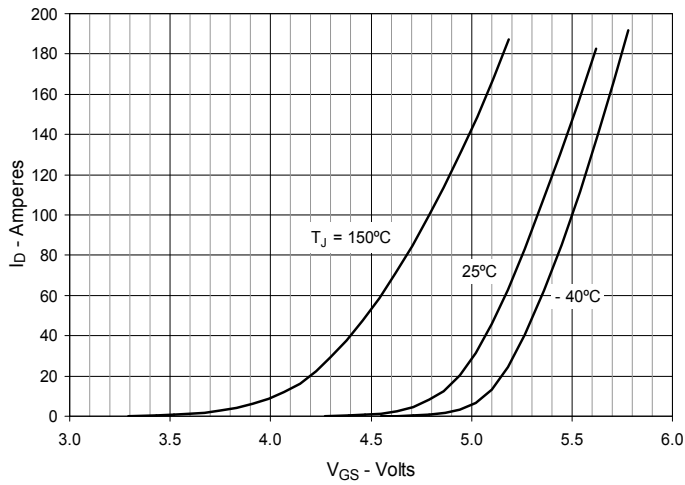
**Fig. 5.  $R_{DS(on)}$  Normalized to  $I_D = 120\text{A}$  Value**  
**vs. Drain Current**



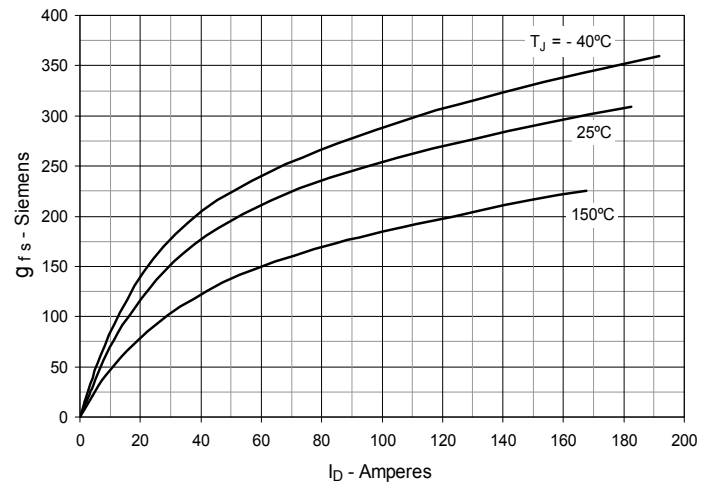
**Fig. 6. Drain Current vs. Case Temperature**



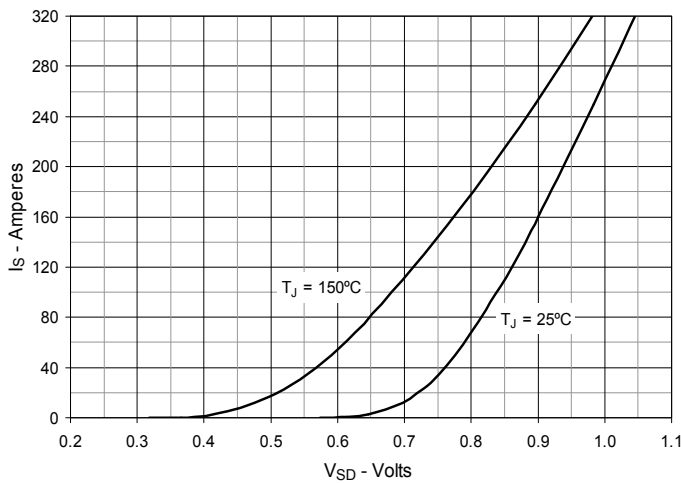
**Fig. 7. Input Admittance**



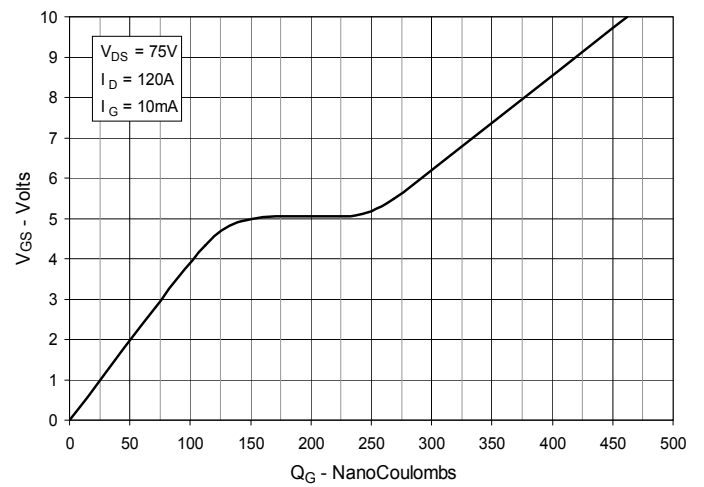
**Fig. 8. Transconductance**



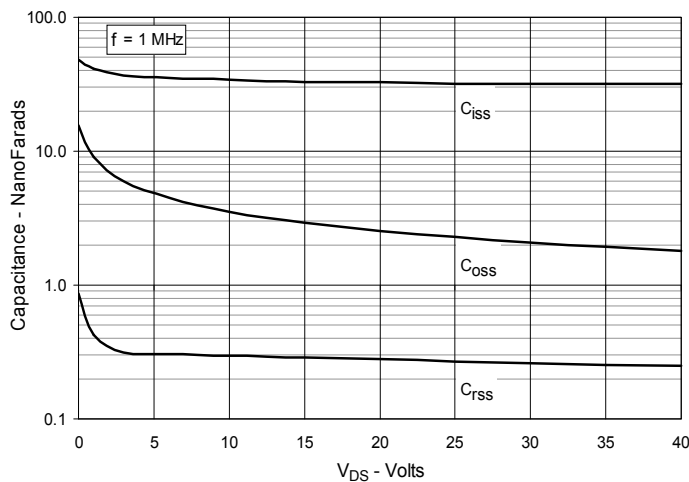
**Fig. 9. Forward Voltage Drop of Intrinsic Diode**



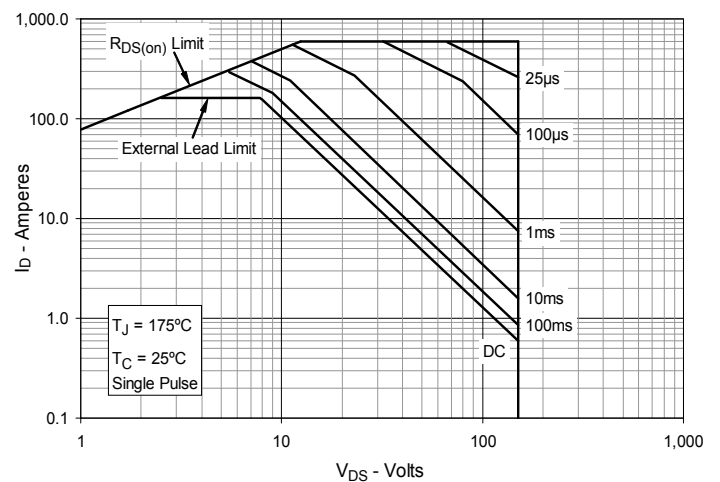
**Fig. 10. Gate Charge**



**Fig. 11. Capacitance**



**Fig. 12. Forward-Bias Safe Operating Area**



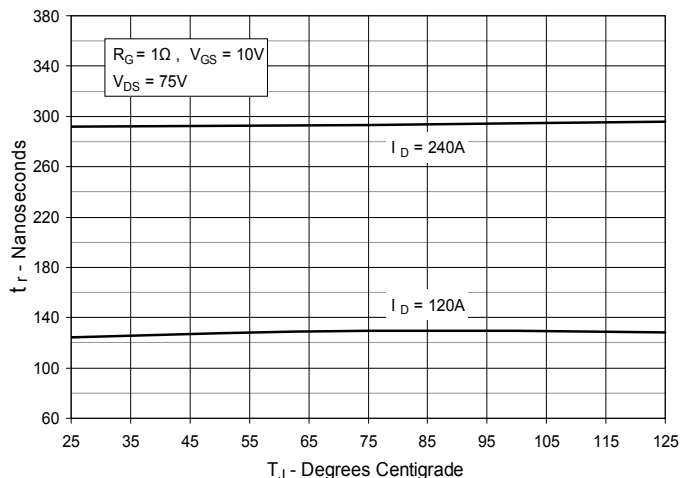
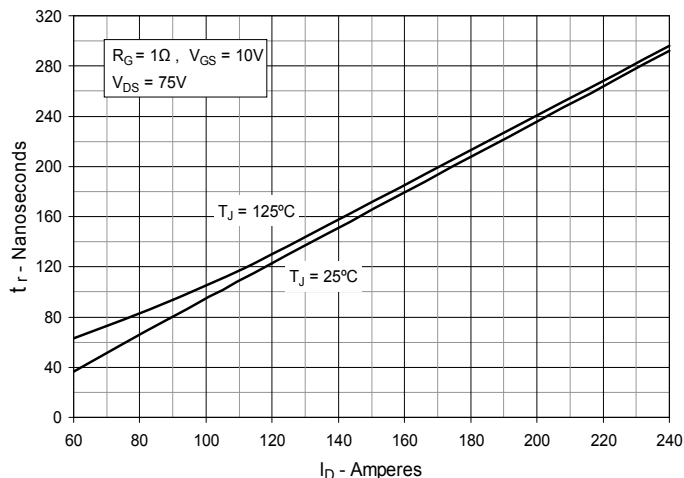
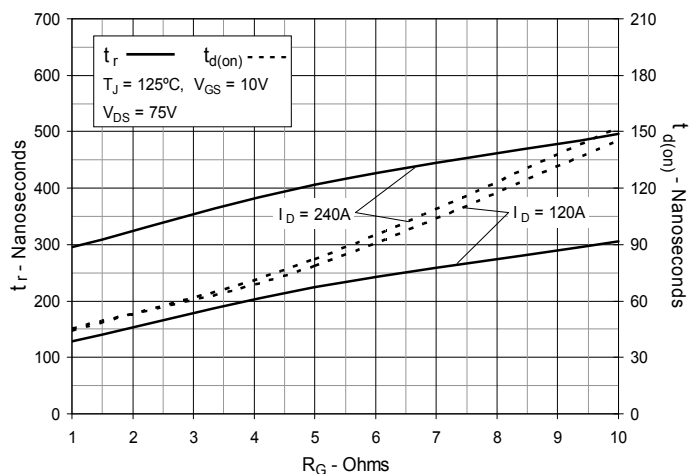
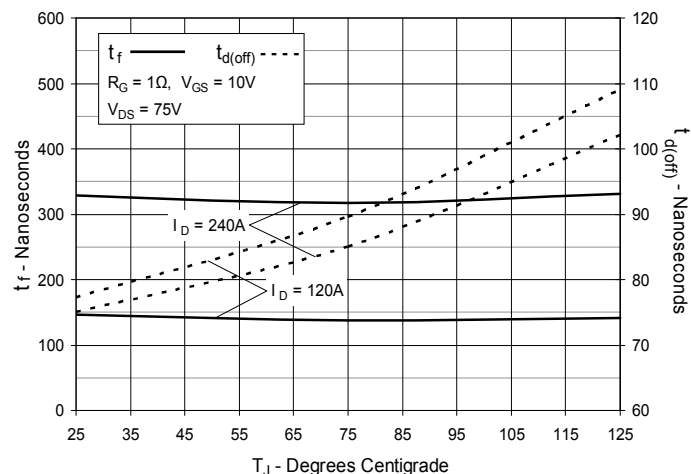
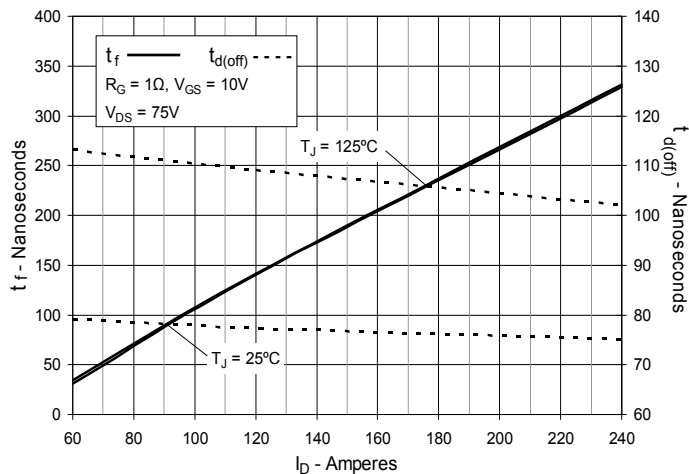
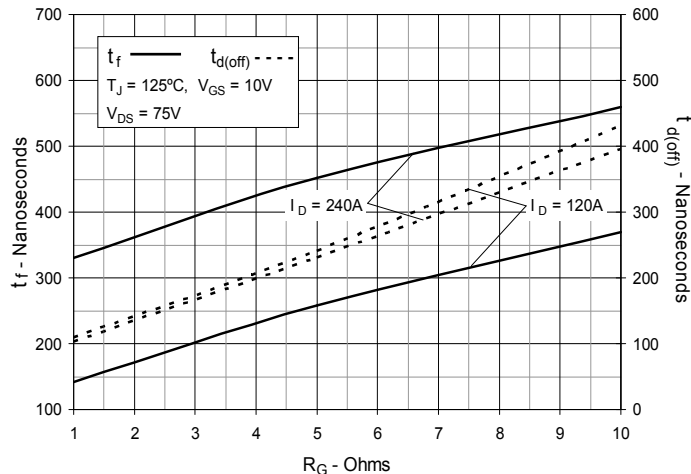
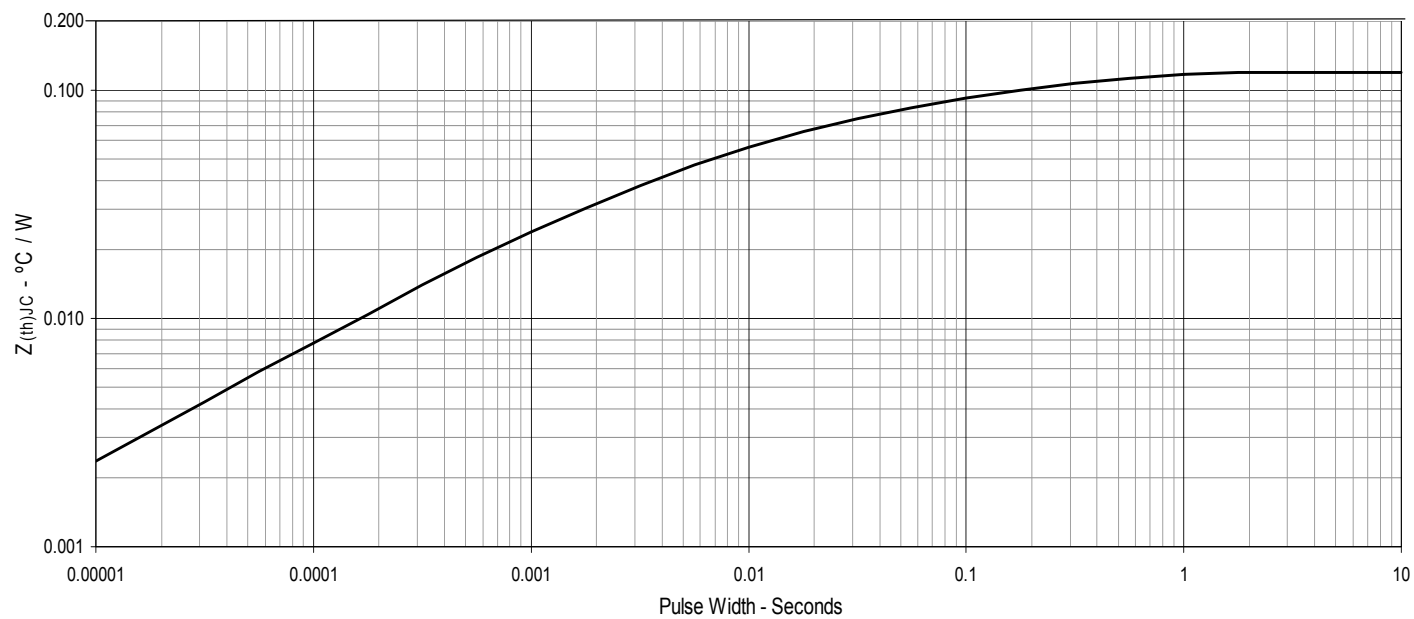
**Fig. 13. Resistive Turn-on Rise Time vs. Junction Temperature**

**Fig. 14. Resistive Turn-on Rise Time vs. Drain Current**

**Fig. 15. Resistive Turn-on Switching Times vs. Gate Resistance**

**Fig. 16. Resistive Turn-off Switching Times vs. Junction Temperature**

**Fig. 17. Resistive Turn-off Switching Times vs. Drain Current**

**Fig. 18. Resistive Turn-off Switching Times vs. Gate Resistance**


Fig. 19. Maximum Transient Thermal Impedance





---

Disclaimer Notice - Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at [www.littelfuse.com/disclaimer-electronics](http://www.littelfuse.com/disclaimer-electronics).